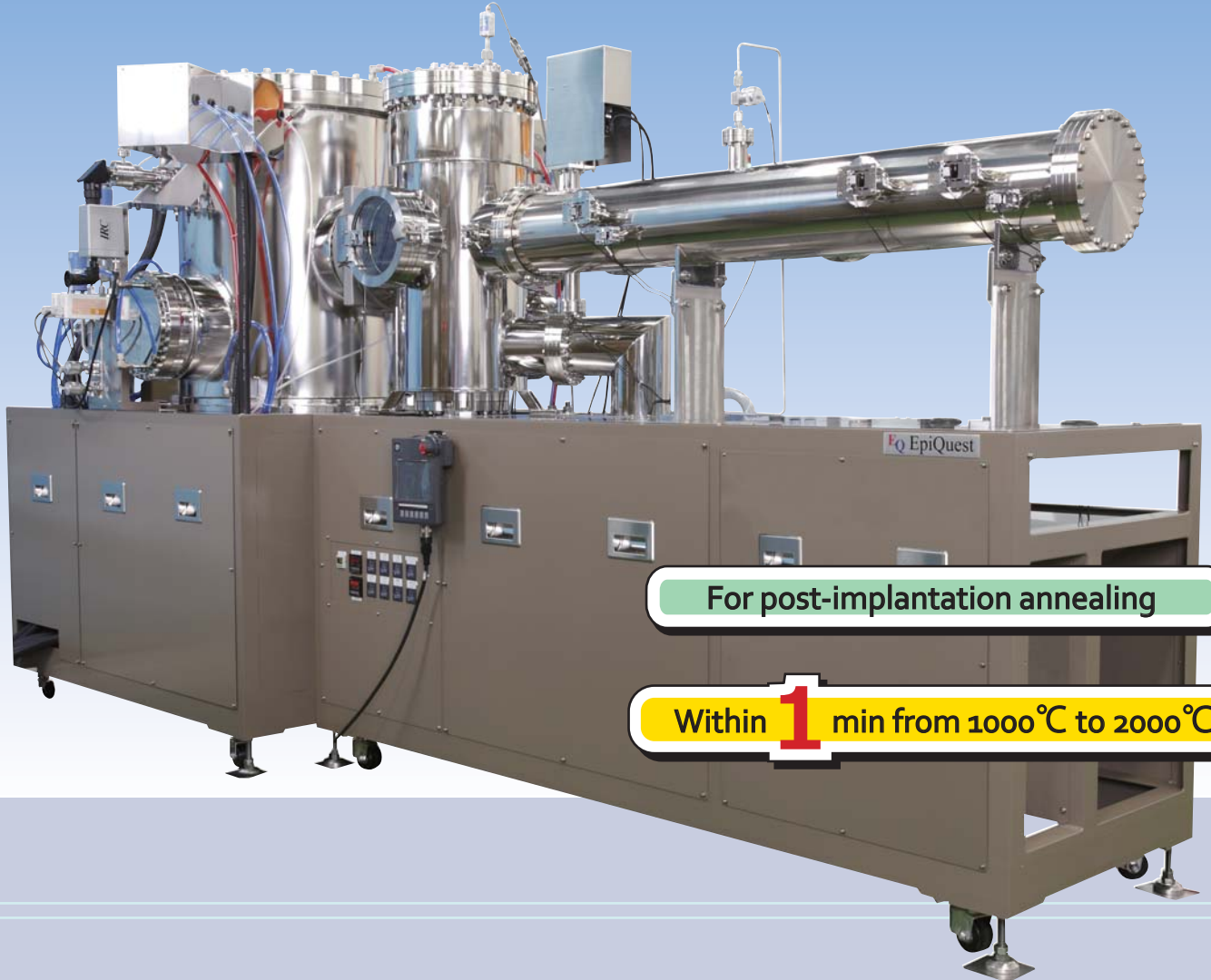


Ultra High Temperature furnace for SiC process

(Type: KGX-2000)



For post-implantation annealing

Within **1** min from 1000°C to 2000°C

*Applications

For post-implantation annealing
For surface treatment

*Specifications

Heating: Resistance heating
Uniform heating zone: 160mmΦX 65mmH
Crucible: TaC/Ta (EVEREDKOTE-K by TOYO TANSO)
Wafer Size: up to 6inch
Maximum heating Temperature: 2200°C
Heating Rate : Within 1min from 1000°C to 2000°C



Crucible: TaC/Ta
(EVEREDKOTE-K by TOYO TANSO)